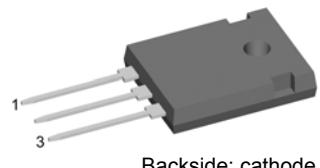
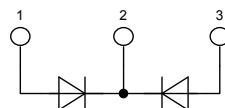


HiPerFRED²

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

Part number

DPF 60 C 300 HB



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

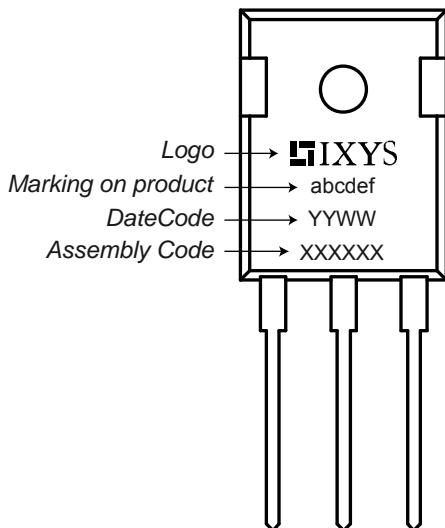
Symbol	Definition	Conditions		Ratings		
				min.	typ.	max.
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^\circ\text{C}$			300 V
I_R	reverse current	$V_R = 300\text{V}$	$T_{VJ} = 25^\circ\text{C}$		5 μA	
		$V_R = 300\text{V}$	$T_{VJ} = 150^\circ\text{C}$		0.25 mA	
V_F	forward voltage	$I_F = 30\text{A}$	$T_{VJ} = 25^\circ\text{C}$		1.16 V	
		$I_F = 60\text{A}$			1.34 V	
		$I_F = 30\text{A}$	$T_{VJ} = 150^\circ\text{C}$		0.97 V	
		$I_F = 60\text{A}$			1.18 V	
I_{FAV}	average forward current	rectangular	$d = 0.5$	$T_c = 140^\circ\text{C}$		30 A
V_{FO}	threshold voltage	$\left. \begin{array}{l} \text{slope resistance} \\ \text{for power loss calculation only} \end{array} \right\}$		$T_{VJ} = 175^\circ\text{C}$		0.72 V
r_F	slope resistance					6.7 m Ω
R_{thJC}	thermal resistance junction to case					0.95 K/W
T_{VJ}	virtual junction temperature			-55	175	$^\circ\text{C}$
P_{tot}	total power dissipation					160 W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$ (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		400 A
I_{RM}	max. reverse recovery current			$T_{VJ} = 25^\circ\text{C}$		5 A
		$I_F = 30\text{A}; V_R = 100\text{V}$		$T_{VJ} = \text{ }^\circ\text{C}$		tbd A
t_{rr}	reverse recovery time	$-di_F/dt = 200\text{ A}/\mu\text{s}$		$T_{VJ} = 25^\circ\text{C}$	55 ns	
				$T_{VJ} = \text{ }^\circ\text{C}$	tbd	ns
C_J	junction capacitance	$V_R = 150\text{V}; f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$	50 pF	

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per pin ¹⁾			50	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Product Marking



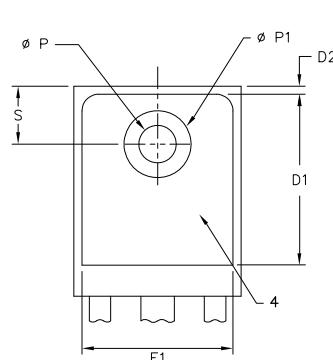
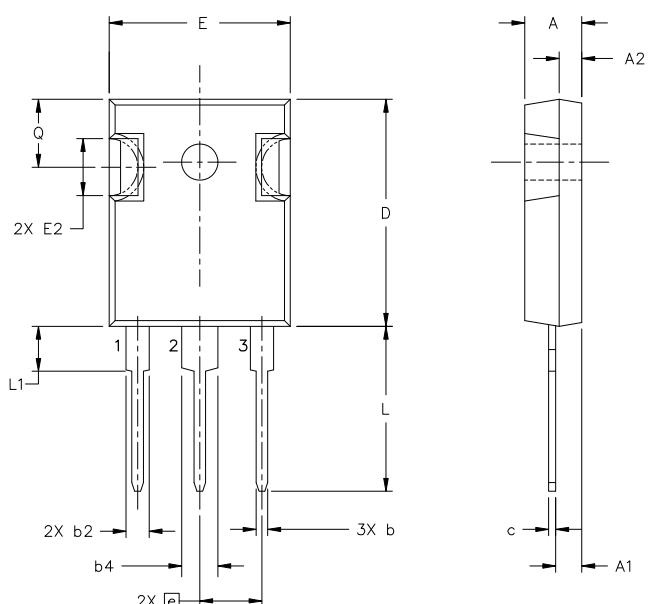
Part number

D = Diode
 P = HiPerFRED
 F = ultra fast
 60 = Current Rating [A]
 C = Common Cathode
 300 = Reverse Voltage [V]
 HB = TO-247AD (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPF 60 C 300 HB	DPF60C300HB	Tube	30	506882

Similar Part	Package	Voltage Class
DPG60C300HB	TO-247	300
DPG60C300QB	TO-3P	300
DPG60C300PC	TO-263 (D2Pak)	300
DPG60C300HJ	ISOPLUS247	300
DPG80C300HB	TO-247	300

Outlines TO-247



Symbol	Inches		Millimeters	
	min	max	min	max
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
ØP	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530		13.45	-
ØP1	-	0.291	-	7.39